Claim Amendments:

Please amend the claims as indicated:

Claims 1-52 (Canceled).

53. (Original) A method of processing ESD dissipative ceramics comprising the steps of:

(a) consolidating two or more powders to a final density by one or heat treatments, and

(b) using a final heat treatment to produce at least a 25% change in the resistivity of the resulting ceramic.

54. (Original) The process of Claim 53, wherein the final heat treatment is conducted in air at less than 90% of the sintering temperature.

55. (Original) The process of Claim 53, wherein the final heat tretment is conducted in oxygen at a partial pressure less than that of atmospheric oxygen.

56. (Original) The process of Claim 53, wherein the final heat treatment increases the resistance of the resulting ceramic.

57. (Original) The process of Claim 53, wherein the final heat treatment decreases the resistance of the resulting ceramic.

58. (Original) The process of Claim 53, wherein the final heat treatment moves volume resistivity into the range 10^6 - 10^9 ohm-cm.

59. (Original) A method of forming light colored ESD dissipative ceramics comprising the steps of:

(a) forming a mixture comprising from about 85 to 60 vol.% Y-TZP and from about 15 to 40 vol.% ZnO; and

(b) densifying the mixture to at least 95% of the theoretical density by a primary heat treatment.

60. (Currently amended) The method of Claim 59, further comprising employing a secondary heat treatment step to increase the ~~theoretical~~ density to greater than 99% <u>of theoretical density</u>.

61. (Original) A method of forming light colored ESD dissipative ceramics comprising the steps of:

(a) forming a mixture comprising from about 90 to 50 vol.% Y-TZP and from about 10 to 50 vol.% semi-conductive SnO_2; and

(b) densifying the mixture to at least 95% of the theoretical density by a primary heat treatment.

62. (Currently amended) The method of Claim 61, further comprising employing a secondary heat treatment step to increase the ~~theoretical~~ density to greater than 99% <u>of theoretical density</u>.

63. (Original) A method of modifying the resistivity of ESD dissipative ceramics comprising the step of hot isostatic pressing said ceramics under controlled conditions of heat and atmosphere.

64. (Currently amended) A method of forming ceramic-based components for ESD-dissipative purposes comprising the steps of:

(a) forming an ESD dissipative ~~composition~~ <u>component</u>;

(b) forming the desired surface finish on said ~~composition~~ <u>component</u>; and

(c) forming ceramic-based components either in whole or in part, in which the ceramics produce less than 600 particles/cm^2 ~~in the particle~~ <u>in a particle</u> generation test for ESD-dissipative purposes.

65. (Original) The method of Claim 64, wherein the surface finish is formed by tumbling.

66. (Original) The method of Claim 64, wherein the entire component is formed from the ESD dissipative ceramic composition.

67. (Original) The method of Claim 64, wherein only a portion of the component is formed from the ESD dissipative ceramic composition.

68. (Original) An ESD dissipative component, formed by the method of Claim 64, wherein the component is selected from the group consisting of MR (magnetoresistive) head substrates, transfer tools for magnetic head manufacturing, tools, fixtures, and containers for HGA (head gimbal assembly), HSA (head stack assembly), HDD (hard disk drive) assembly, tools, fixtures, and containers for wafer handling, processing, and cleaning, tools, fixtures, and containers for wire bonding, trimming, cutting, pick-and-place nozzles for IC chip handling, nozzles for adhesive and solder dispensing, wafer handling fixtures, end effectors, vacuum chucks, IC handling and test fixtures, tools, fixtures, and containers for ESD sensitive devices, assembly fixtures for IC's and magnetic heads, tweezers, screw drivers, scissors, blades, parts for robotic fingers, tools, fixtures, and containers for electro-optic coating process, tools, fixtures, and containers for reticles (photo mask).

Claims 69-77 (Canceled).

78. (New) A method of forming and ESD dissipative ceramic component, comprising the steps of:

sintering a composition comprising a base material comprising tetragonal zirconia and a resistivity modifier comprising 5 vol% to about 60 vol% of the base material, the resistivity modifier selected from conductive and semiconductive materials and mixtures thereof, to form a sintered body; and

hot isostatic pressing the sintered body to form an ESD dissipative ceramic component having a volume resistivity within a rang of 10^3 to 10^{11} Ohm-cm.

79. (New) A method of forming an ESD dissipative ceramic component, comprising the steps of:

heat treating a ceramic green body to densify the green body and form a densified component, the green body comprising a base material comprising tetragonal ziconia and a resistivity modifier; and

adjusting a resistivty of the densified component by annealing the densified component.

80. (New) The method of claim 79, wherein the resistivity modifier comprises about 5 vol% to about 60 vol% of the base material, the resistivity modifier selected from conductive and semiconductive materials and mixtures thereof.

81. (New) The method of claim 79, wherein the step of adjusting the resistivity is carried out by annealing to change an equilibrium density of charge carriers.

82. (New) The method of claim 79, wherein heat treating is carried out by sintering.

83. (New) The method of claim 82, wherein the sintering step is carried out by pressureless sintering.

84. (New) The method of claim 79, wherein heat treating is carried out by sintering and hot pressing.

85. (New) The method of claim 84, wherein hot pressing comprises hot isostatic pressing.

86. (New) The method of claim 79, wherein heat treating is carried out at a first temperature, and annealing is carried out at a second temperature, the second temperature being less than 90% of the first temperature.

87. (New) The method of claim 86, wherein the second temperature is within a range of about 560 °C to 890 °C.

88. (New) The method of claim 79, wherein the resistivity is adjusted by at least 25%.